NPN Silicon Epitaxial Planar Transistor

for 1W Output, Electronic Governor, DC-DC Converter Applications.

The transistor is subdivided into four groups D, E, F and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	25	V
Collector Emitter Voltage	V _{CEO}	20	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ic	700	mA
Collector Current (Pulse)	I _{CP}	1500	mA
Power Dissipation	P _{tot}	600	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°C













ST 2SD734

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =2V, I _C =50mA					
Current Gain Group	D h _{FE}	60	-	120	-
	E h _{FE}	100	-	200	-
	F h _{FE}	160	-	320	-
	G h _{FE}	280	-	560	-
at V _{CE} =2V, I _C =500mA	h _{FE}	50	-	-	-
Collector Cutoff Current					
at V _{CB} =20V	I _{CBO}	-	-	1	μА
Emitter Cutoff Current					
at V _{EB} =4V	I _{EBO}	-	-	1	μΑ
Gain Bandwidth Product					
at V _{CE} =10V, I _C =50mA	f _T	-	250	-	MHz
Output Capacitance					
at V _{CB} =10V,f=1MHz	$C_{\sf ob}$	-	8	-	pF









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